

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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## Silicon Power Schottky Diode

$V_{RRM} = 20 \text{ V} - 100 \text{ V}$   
 $I_F = 200 \text{ A}$

### Features

- High Surge Capability
- Types up to 100 V  $V_{RRM}$

**Twin Tower Package**



**Maximum ratings, at  $T_j = 25 \text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

Parameter	Symbol	Conditions	MBR20020CT (R)	MBR20030CT (R)	MBR20035CT (R)	MBR20040CT (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		20	30	35	40	V
RMS reverse voltage	$V_{RMS}$		14	21	25	28	V
DC blocking voltage	$V_{DC}$		20	30	35	40	V
Continuous forward current	$I_F$	$T_C \leq 136 \text{ }^\circ\text{C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}, t_p = 8.3 \text{ ms}$	1500	1500	1500	1500	A
Operating temperature	$T_j$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

**Electrical characteristics, at  $T_j = 25 \text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MBR20020CT (R)	MBR20030CT (R)	MBR20035CT (R)	MBR20040CT (R)	Unit
Diode forward voltage	$V_F$	$I_F = 100 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	0.65	0.65	0.65	0.65	V
Reverse current	$I_R$	$V_R = 20 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$ $V_R = 20 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	5 200	5 200	5 200	5 200	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.5	0.5	0.5	0.5	$^\circ\text{C/W}$
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